

MGFC40V6472

6.4~7.2GHz BAND 10W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC40V6472 is an internally impedance-matched GaAs power FET especially designed for use in 6.4~7.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

- Class A operation
- Internally matched to 50Ω system
- High output power
 $P_{1dB} = 10W$ (TYP) @ 6.4~7.2GHz
- High power gain
 $G_{LP} = 8$ dB (TYP) @ 6.4~7.2GHz
- High power added efficiency
 $\eta_{add} = 32\%$ (TYP) @ 6.4~7.2GHz, P_{1dB}
- Hermetically sealed metal-ceramic package
- Low distortion [Item: -51]
 $IM_3 = -45$ dBc (TYP) @ $P_o = 29$ (dBm) S.C.L.

APPLICATION

- Item-01: 6.4~7.2GHz band power amplifier
- Item-51: Digital radio communication

QUALITY GRADE

- IG

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Symbol	Parameter	Ratings	Unit
V _{GD0}	Gate to drain voltage	-15	V
V _{GSO}	Gate to source voltage	-15	V
I _D	Drain current	6	A
I _{GR}	Reverse gate current	-20	mA
I _{GF}	Forward gate current	42	mA
P _T	Total power dissipation *1	42.8	W
T _{ch}	Channel temperature	175	°C
T _{stg}	Storage temperature	-65 ~ +175	°C

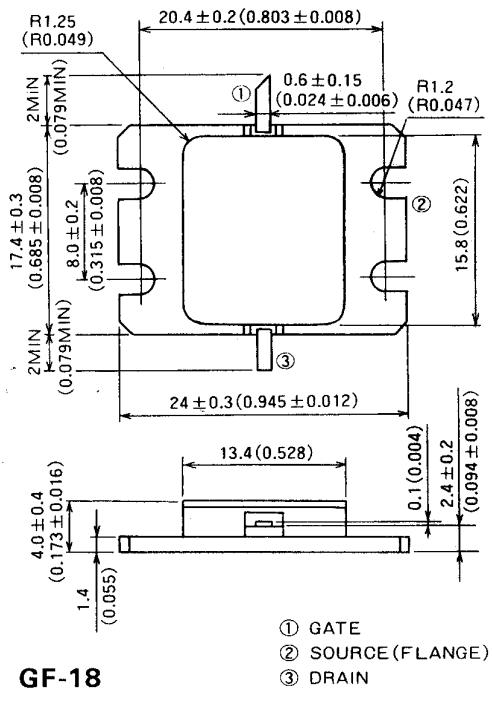
*1: T_C = 25°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
I _{DSS}	Saturated drain current	V _{DS} = 3V, V _{GS} = 0V	—	4.5	6	A
g _m	Transconductance	V _{DS} = 3V, I _D = 2.2A	—	2	—	S
V _{GS(off)}	Gate to source cut-off voltage	V _{DS} = 3V, I _D = 40mA	-2	-3	-4	V
P _{1dB}	Output power at 1dB gain compression	V _{DS} = 10V, I _D = 2.4A, f = 6.4~7.2GHz	39.5	40.5	—	dBm
G _{LP}	Linear power gain		7	8	—	dB
I _D	Drain current		—	2.4	—	A
η _{add}	Power added efficiency		—	32	—	%
IM ₃	3rd order IM distortion *1		-42	-45	—	dBc
R _{th(gh-c)}	Thermal resistance *2		ΔV _f method	—	—	3.5

*1: Item-51, 2-tone test P_o = 29 dBm Single Carrier Level f = 7.2GHz Δf = 10 MHz. *2: Channel to case

OUTLINE DRAWING Unit: millimeters (inches)



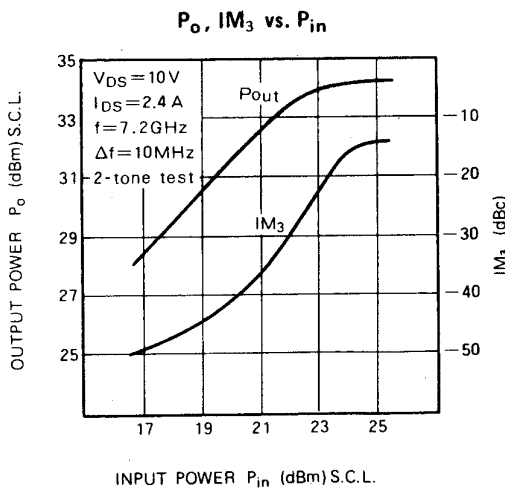
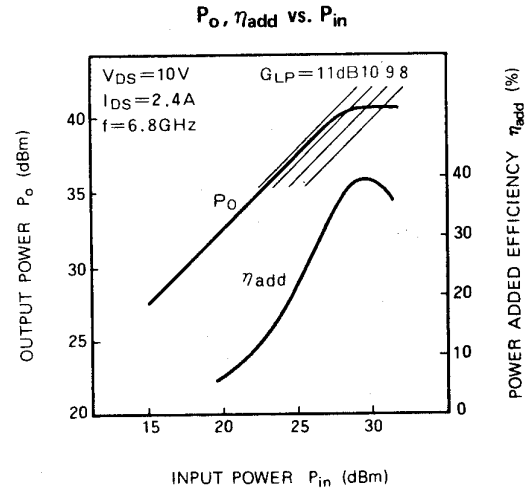
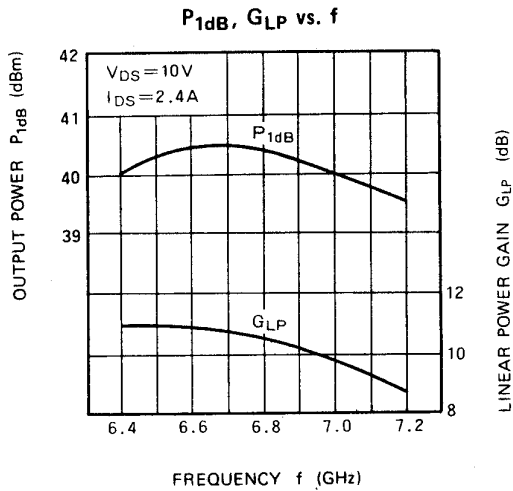
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RECOMMENDED BIAS CONDITIONS

- V_{DS} = 10V
- I_D = 2.4A
- R_g = 50Ω
- Refer to Bias Procedure

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TYPICAL CHARACTERISTICS



S PARAMETERS ($T_a=25^\circ C$, $V_{DS}=10V$, $I_{DS}=2.4A$)

f (GHz)	S Parameters (TYP.)							
	S_{11}		S_{21}		S_{12}		S_{22}	
	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)
6.4	0.40	-170.9	3.51	34.3	0.071	-24.8	0.32	-134.4
6.5	0.41	140.3	3.51	-6.5	0.072	-65.4	0.31	-171.2
6.6	0.40	92.6	3.47	-47.4	0.073	-106.6	0.29	-155.1
6.7	0.39	41.3	3.43	-88.0	0.073	-147.2	0.26	123.6
6.8	0.40	-15.1	3.39	-129.5	0.073	171.2	0.21	95.4
6.9	0.44	-76.5	3.27	-173.5	0.071	127.6	0.14	77.0
7.0	0.45	-90.0	3.05	175.0	0.071	100.0	0.13	60.0
7.1	0.47	-110.0	2.92	165.0	0.070	80.0	0.15	50.0
7.2	0.49	-130.0	2.75	155.0	0.070	60.0	0.19	40.0